

P-Channel 1.25-W, 1.8-V (G-S) MOSFET

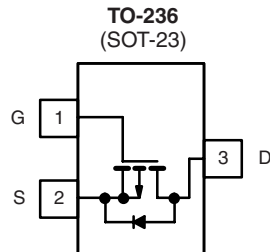
| PRODUCT SUMMARY | | |
|-----------------|-----------------------------|-----------|
| V_{DS} (V) | $R_{DS(on)}$ (Ω) | I_D (A) |
| - 8 | 0.052 at $V_{GS} = - 4.5$ V | ± 3.5 |
| | 0.071 at $V_{GS} = - 2.5$ V | ± 3 |
| | 0.108 at $V_{GS} = - 1.8$ V | ± 2 |

FEATURES

- Halogen-free According to IEC 61249-2-21 Available
- TrenchFET® Power MOSFETs: 1.8 V Rated



Available
RoHS*
COMPLIANT
HALOGEN
FREE
Available



Top View
Si2305DS (A5)*
* Marking Code

Ordering Information: Si2305DS-T1
Si2305DS-T1-E3 (Lead (Pb)-free)
Si2305DS-T1-GE3 (Lead (Pb)-free and Halogen-free)

| ABSOLUTE MAXIMUM RATINGS $T_A = 25$ °C, unless otherwise noted | | | |
|--|----------------|---------------|-----------|
| Parameter | Symbol | Limit | Unit |
| Drain-Source Voltage | V_{DS} | - 8 | V |
| Gate-Source Voltage | V_{GS} | ± 8 | |
| Continuous Drain Current ($T_J = 150$ °C) | I_D | $T_A = 25$ °C | ± 3.5 |
| | | $T_A = 70$ °C | ± 2.8 |
| Pulsed Drain Current | I_{DM} | ± 12 | A |
| Continuous Source Current (Diode Conduction) ^{a, b} | I_S | - 1.6 | |
| Maximum Power Dissipation ^{a, b} | P_D | $T_A = 25$ °C | 1.25 |
| | | $T_A = 70$ °C | 0.8 |
| Operating Junction and Storage Temperature Range | T_J, T_{stg} | - 55 to 150 | °C |

| THERMAL RESISTANCE RATINGS | | | | | |
|--|------------|--------------|---------|------|--|
| Parameter | Symbol | Typical | Maximum | Unit | |
| Maximum Junction-to-Ambient ^a | R_{thJA} | $t \leq 5$ s | 100 | °C/W | |
| | | Steady State | 130 | | |

Notes:

- a. Surface Mounted on FR4 board.
b. $t \leq 5$ s.

* Pb containing terminations are not RoHS compliant, exemptions may apply.

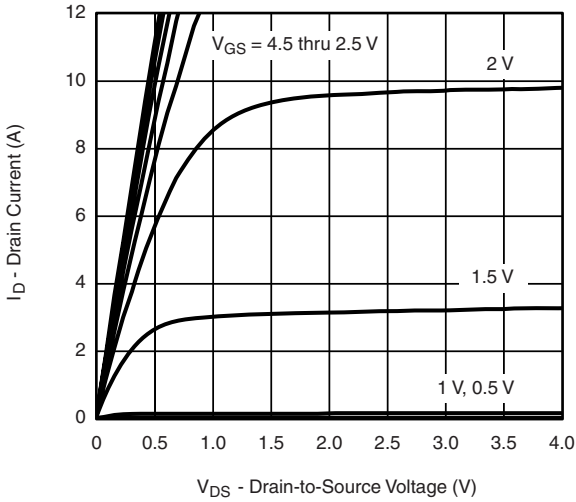
| SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted | | | | | | |
|---|---------------|--|--------|-------|-----------|---------------|
| Parameter | Symbol | Test Conditions | Limits | | | Unit |
| | | | Min. | Typ. | Max. | |
| Static | | | | | | |
| Drain-Source Breakdown Voltage | $V_{(BR)DSS}$ | $V_{GS} = 0\text{ V}, I_D = -10\text{ }\mu\text{A}$ | - 8 | | | V |
| Gate-Threshold Voltage | $V_{GS(th)}$ | $V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$ | - 0.45 | | - 0.8 | V |
| Gate-Body Leakage | I_{GSS} | $V_{DS} = 0\text{ V}, V_{GS} = \pm 8\text{ V}$ | | | ± 100 | nA |
| Zero Gate Voltage Drain Current | I_{DSS} | $V_{DS} = -8\text{ V}, V_{GS} = 0\text{ V}$ | | | - 1 | μA |
| | | $V_{DS} = -8\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$ | | | - 10 | |
| On-State Drain Current ^a | $I_{D(on)}$ | $V_{DS} \leq -5\text{ V}, V_{GS} = -4.5\text{ V}$ | - 6 | | | A |
| | | $V_{DS} \leq -5\text{ V}, V_{GS} = -2.5\text{ V}$ | - 3 | | | |
| Drain-Source On-Resistance ^a | $R_{DS(on)}$ | $V_{GS} = -4.5\text{ V}, I_D = -3.5\text{ A}$ | | 0.044 | 0.052 | Ω |
| | | $V_{GS} = -2.5\text{ V}, I_D = -3\text{ A}$ | | 0.060 | 0.071 | |
| | | $V_{GS} = -1.8\text{ V}, I_D = -2\text{ A}$ | | 0.087 | 0.108 | |
| Forward Transconductance ^a | g_{fs} | $V_{DS} = -5\text{ V}, I_D = -3.5\text{ A}$ | | 8.5 | | S |
| Diode Forward Voltage | V_{SD} | $I_S = -1.6\text{ A}, V_{GS} = 0\text{ V}$ | | | - 1.2 | V |
| Dynamic^b | | | | | | |
| Total Gate Charge | Q_g | $V_{DS} = -4\text{ V}, V_{GS} = -4.5\text{ V}, I_D \cong -3.5\text{ A}$ | | 10 | 15 | nC |
| Gate-Source Charge | Q_{gs} | | | 2 | | |
| Gate-Drain Charge | Q_{gd} | | | 2 | | |
| Input Capacitance | C_{iss} | $V_{DS} = -4\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$ | | 1245 | | pF |
| Output Capacitance | C_{oss} | | | 375 | | |
| Reverse Transfer Capacitance | C_{rss} | | | 210 | | |
| Switching^b | | | | | | |
| Turn-On Time | $t_{d(on)}$ | $V_{DD} = -4\text{ V}, R_L = 4\text{ }\Omega$ $I_D \cong -1.0\text{ A}, V_{GEN} = -4.5\text{ V}, R_G = 6\text{ }\Omega$ | | 13 | 20 | ns |
| | t_r | | | 25 | 40 | |
| Turn-Off Time | $t_{d(off)}$ | | | 55 | 80 | |
| | t_f | | | 19 | 35 | |

Notes:

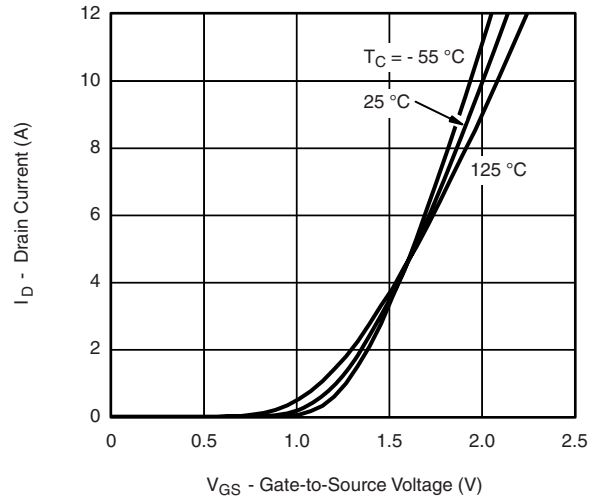
- a. For DESIGN AID ONLY, not subject to production testing.
 b. Pulse test: $PW \leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
 c. Switching time is essentially independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

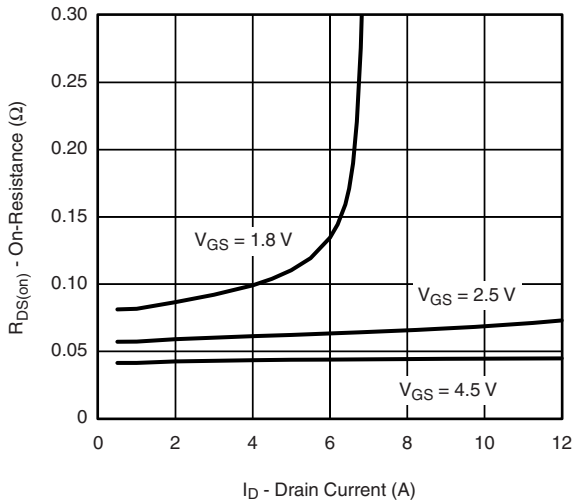
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



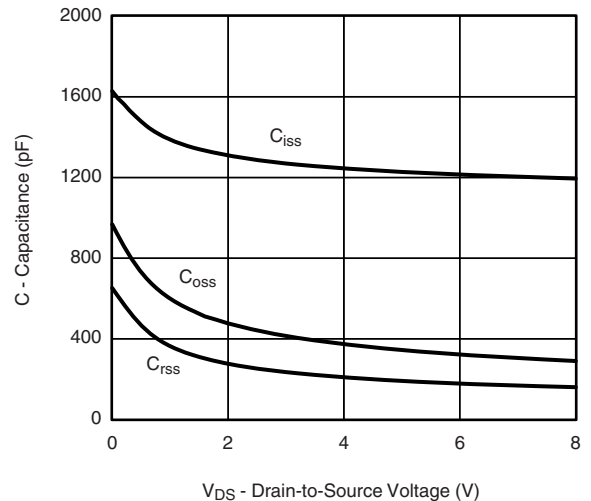
Output Characteristics



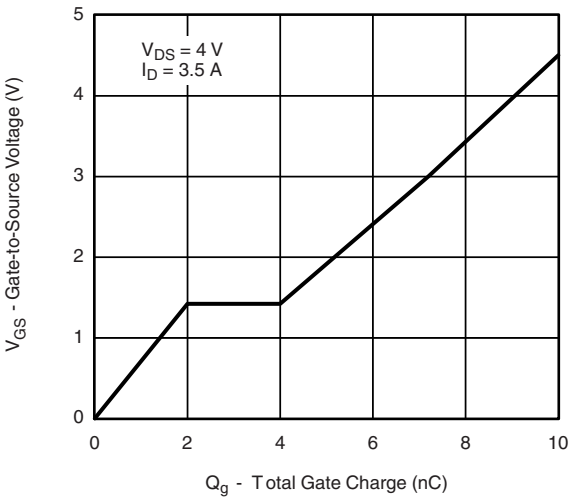
Transfer Characteristics



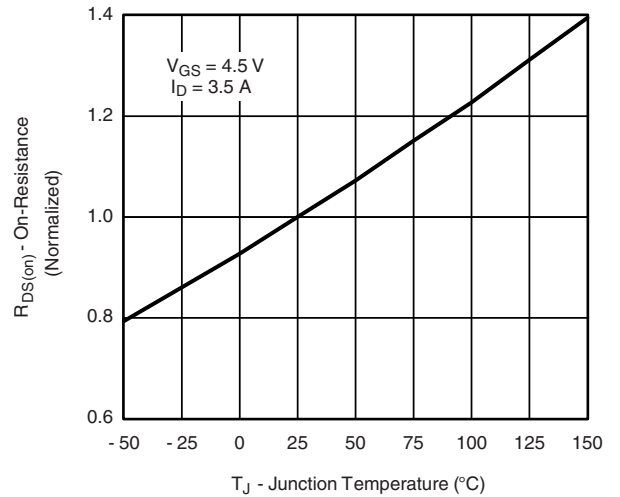
On-Resistance vs. Drain Current



Capacitance

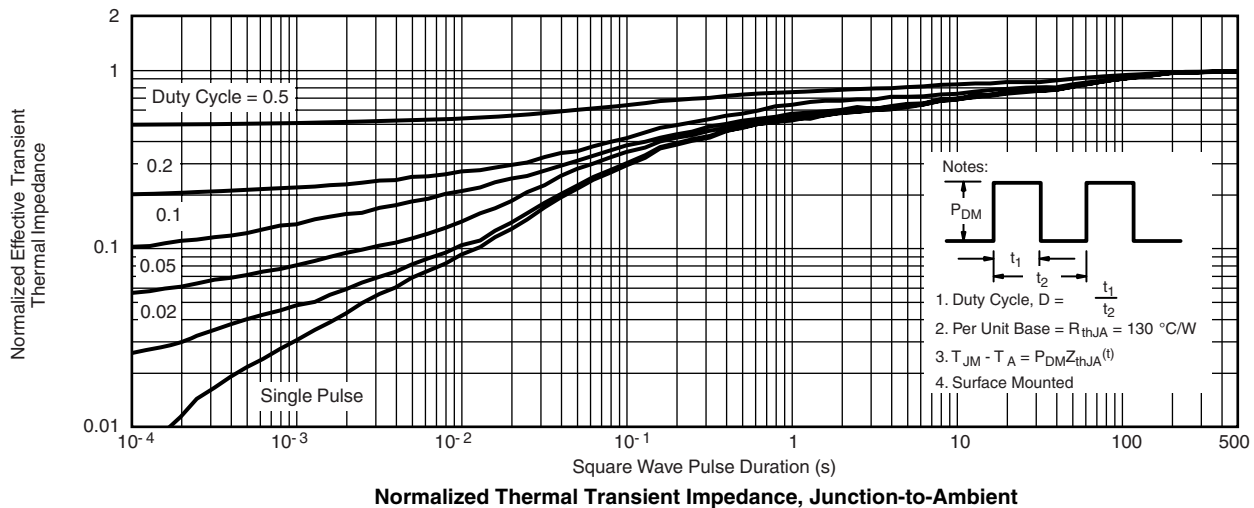
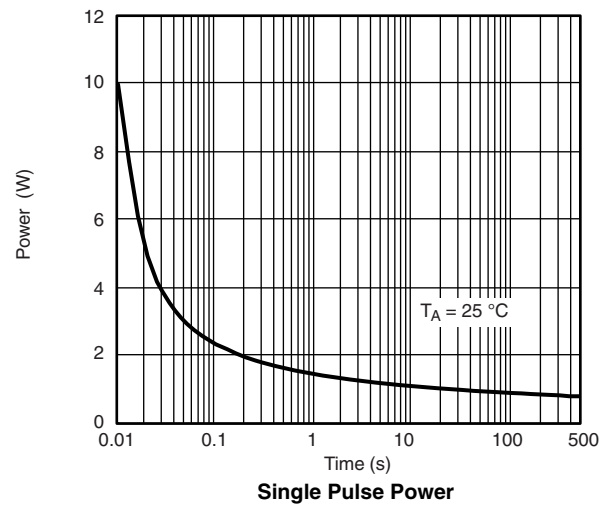
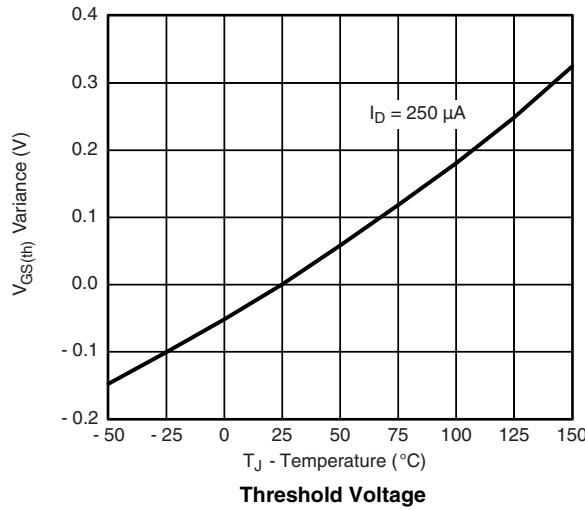
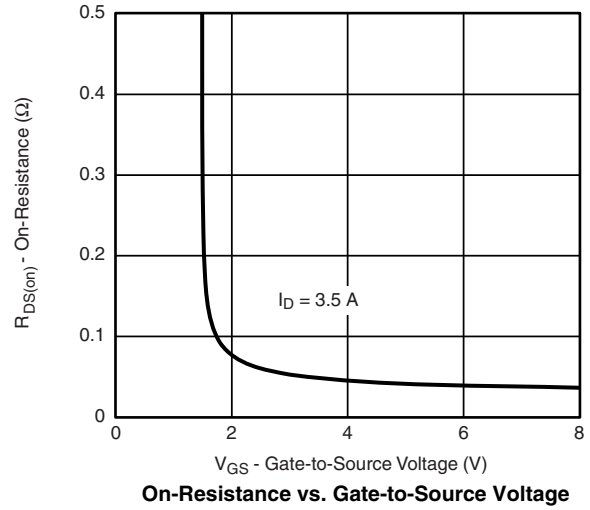
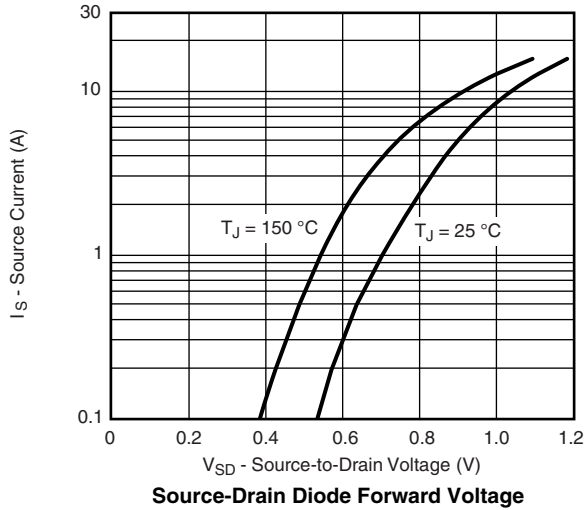


Gate Charge



On-Resistance vs. Junction Temperature

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



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